

BSS138

50V N-Channel MOSFET

0.22A 50V; $R_{DS(ON)typ}=1.0\Omega@10V$, $R_{DS(ON)typ}=1.1\Omega@4.5V$

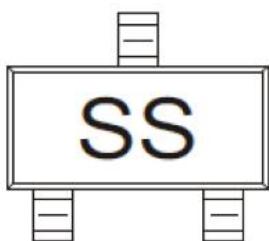
FEATURE

- High density cell design for extremely low $R_{DS(on)}$
- Rugged and Reliable

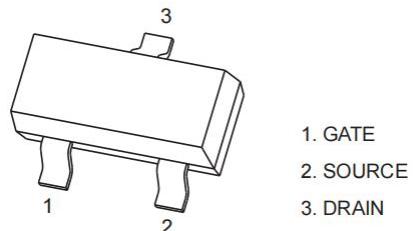
Application

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

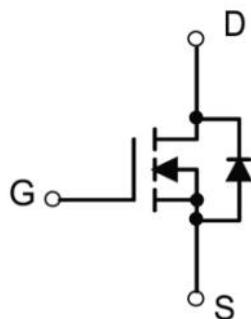
MARKING:



SOT-23



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	0.22	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	R_{JJA}	357	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55~+150	$^\circ C$

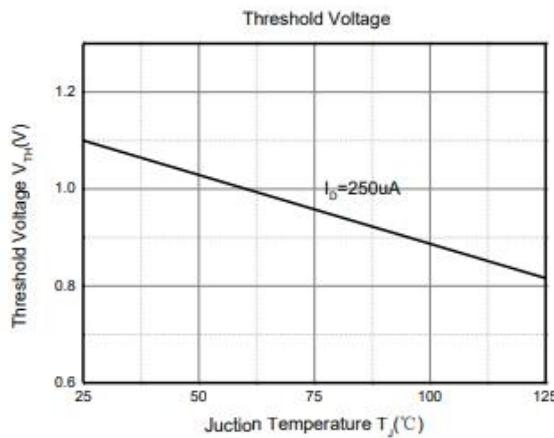
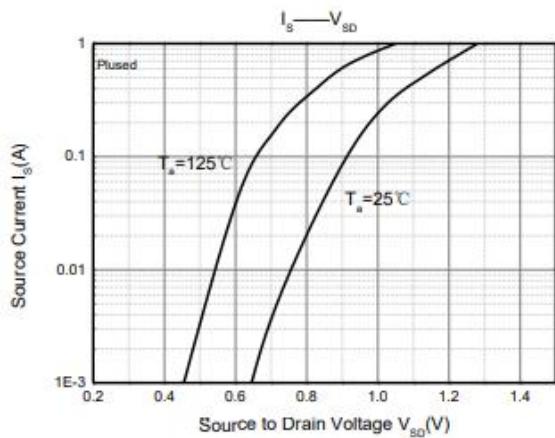
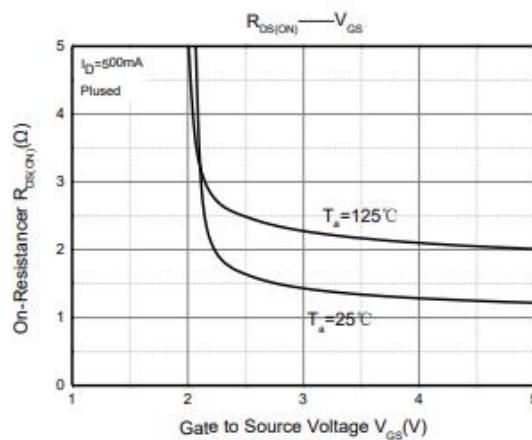
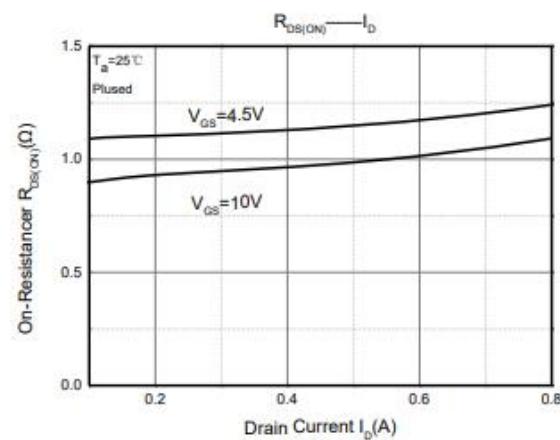
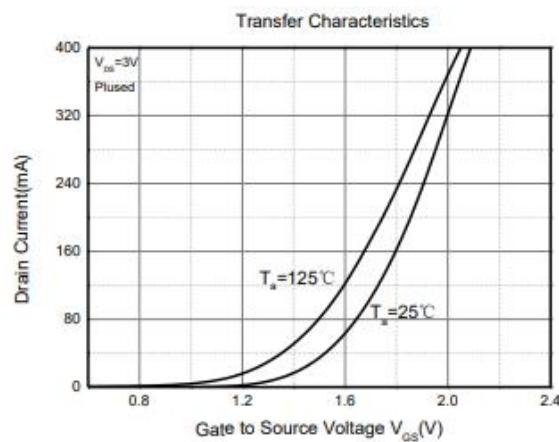
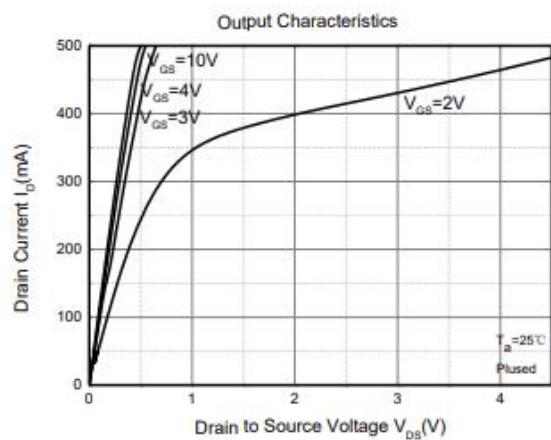
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	50			V
Zero gate voltage drain current	$I_{\text{DSS}1}$	$V_{\text{DS}} = 50\text{V}, V_{\text{GS}} = 0\text{V}$			0.5	μA
	$I_{\text{DSS}2}$	$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 0\text{V}$			100	nA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	nA
Gate threshold voltage ⁽¹⁾	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	0.5	0.95	1.5	V
Drain-source on-resistance ⁽¹⁾	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 0.22\text{A}$		1.0	3.0	Ω
		$V_{\text{GS}} = 4.5\text{V}, I_D = 0.22\text{A}$		1.1	5.0	
Forward transconductance ⁽¹⁾	g_{FS}	$V_{\text{DS}} = 10\text{V}, I_D = 0.22\text{A}$		0.13		S
DYNAMIC CHARACTERISTICS⁽²⁾						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 25\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		26.5		pF
Output Capacitance	C_{oss}			12.9		
Reverse Transfer Capacitance	C_{rss}			5.9		
SWITCHING CHARACTERISTICS^(1,2)						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, V_{\text{DD}} = 30\text{V}, I_D = 0.29\text{A}, R_G = 6\Omega$			5	ns
Turn-on rise time	t_r				18	
Turn-off delay time	$t_{\text{d}(\text{off})}$				36	
Turn-off fall time	t_f				14	
SOURCE-DRAIN DIODE CHARACTERISTICS⁽¹⁾						
Diode Forward Voltage	V_{SD}	$I_S = 0.44\text{A}, V_{\text{GS}} = 0\text{V}$		1.15	1.4	V

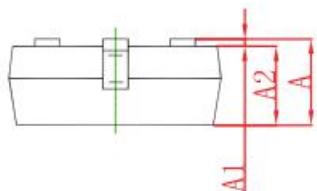
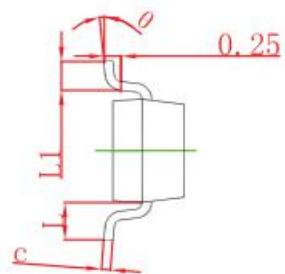
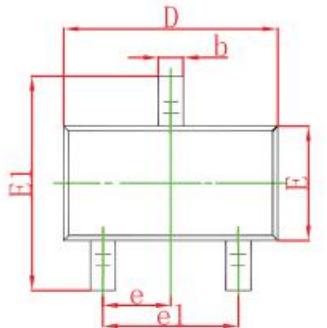
Notes:

1. Pulse Test ; Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
2. These parameters have no way to verify.

Typical Electrical and Thermal Characteristics



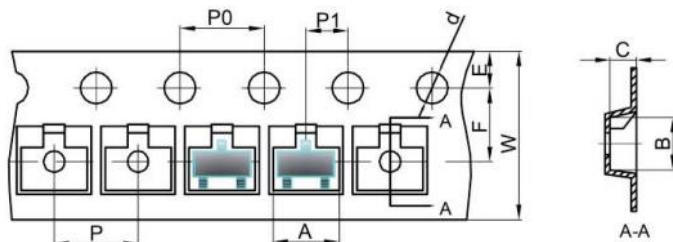
SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

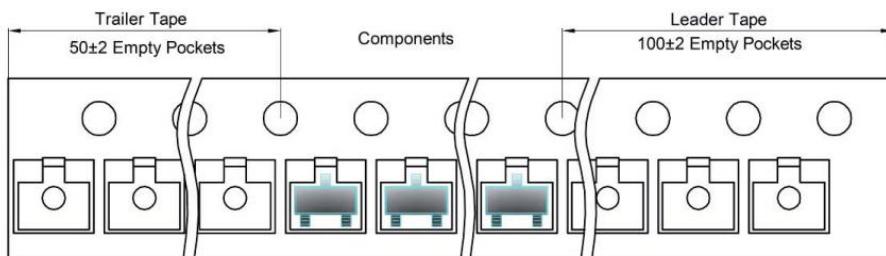
SOT-23 Tape and Reel

SOT-23 Embossed Carrier Tape

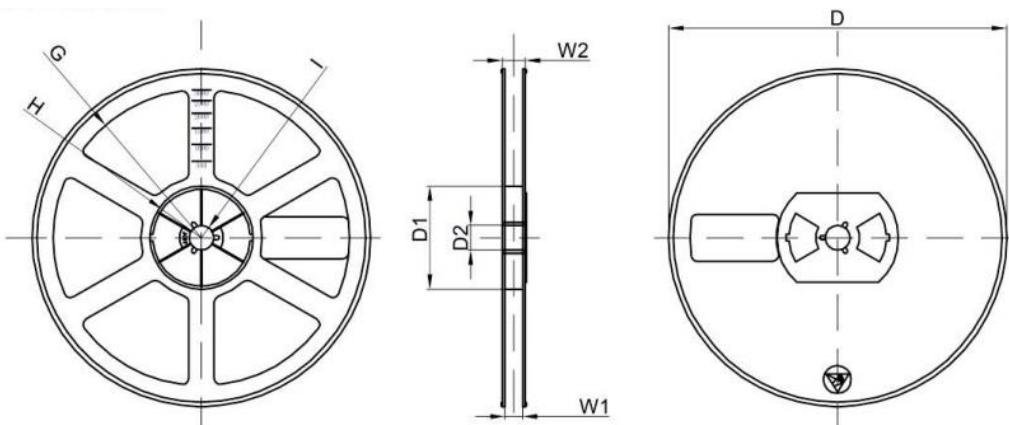


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	